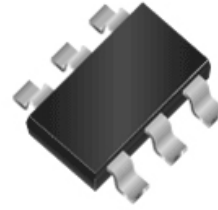


WNM3011

[Http://www.willsemi.com](http://www.willsemi.com)

N-Channel, 30V, 5.7A, Power MOSFET

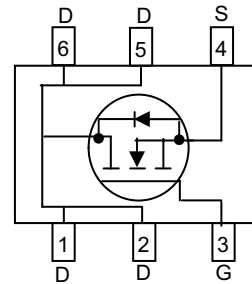
$V_{(BR)DSS}$	$R_{ds(on)}$ (Ω)
30V	0.028@ 10V
	0.039@ 4.5V



SOT-23-6L

Descriptions

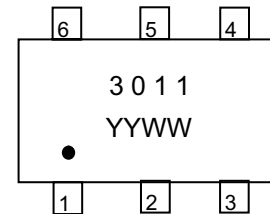
The WNM3011 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in DC-DC conversion and power switch applications. Standard Product WNM3011 is Pb-free.



Configuration (Top View)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-23-6L



3011 = Device Code
 YY =Year
 WW =Week

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order Information

Device	Package	Shipping
WNM3011-6/TR	SOT-23-6L	3000/Tape&Reel

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	5.7	4.9	A
	$T_A=70^\circ\text{C}$		4.6	3.9	
Maximum Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	1.5	1.1	W
	$T_A=70^\circ\text{C}$		0.9	0.7	
Continuous Drain Current ^b	$T_A=25^\circ\text{C}$	I_D	4.9	4.4	A
	$T_A=70^\circ\text{C}$		3.9	3.5	
Maximum Power Dissipation ^b	$T_A=25^\circ\text{C}$	P_D	1.1	0.8	W
	$T_A=70^\circ\text{C}$		0.7	0.5	
Pulsed Drain Current ^c		I_{DM}	20		A
Operating Junction Temperature		T_J	150		$^\circ\text{C}$
Lead Temperature		T_L	260		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150		$^\circ\text{C}$

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10 \text{ s}$	$R_{\theta JA}$	71	82	$^\circ\text{C}/\text{W}$
	Steady State		91	112	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10 \text{ s}$	$R_{\theta JA}$	100	110	
	Steady State		125	139	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	28	40	

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR4 board using minimum pad size, 1oz copper

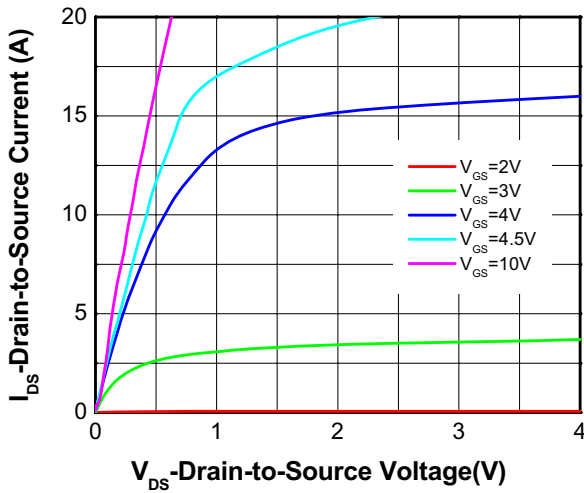
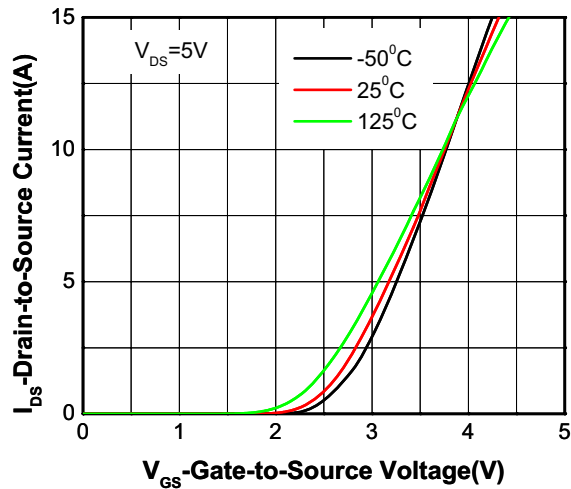
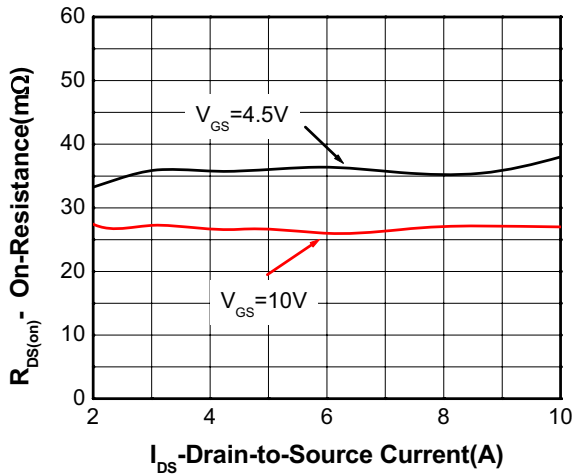
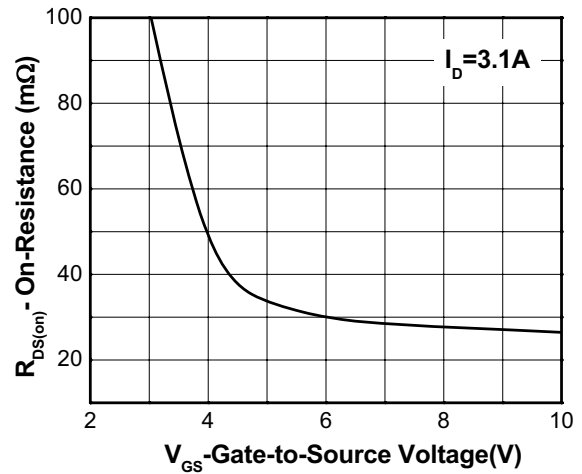
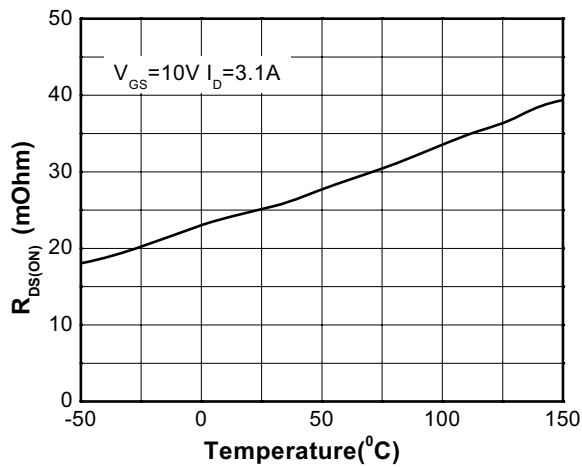
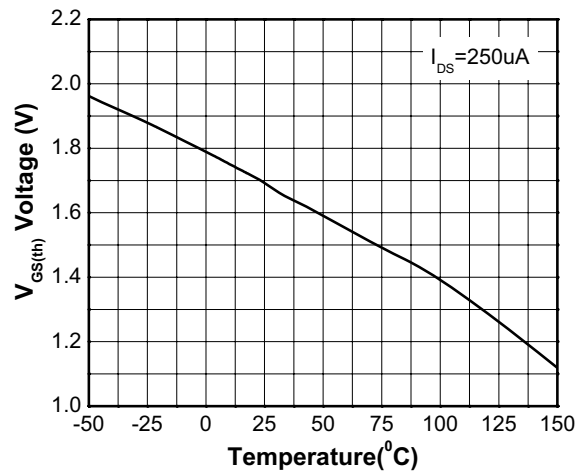
c Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

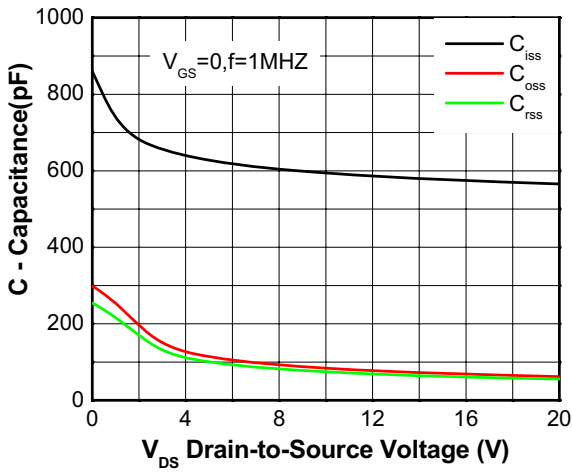
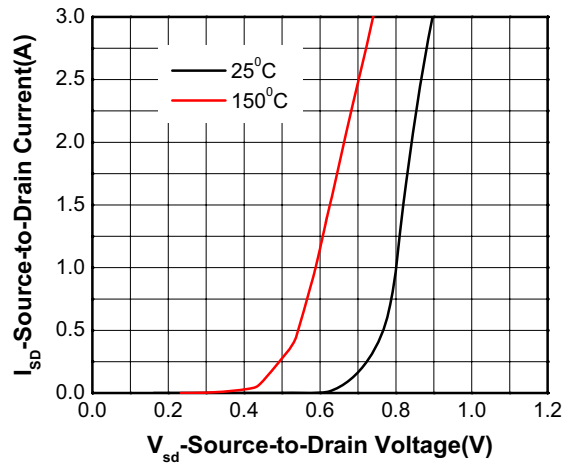
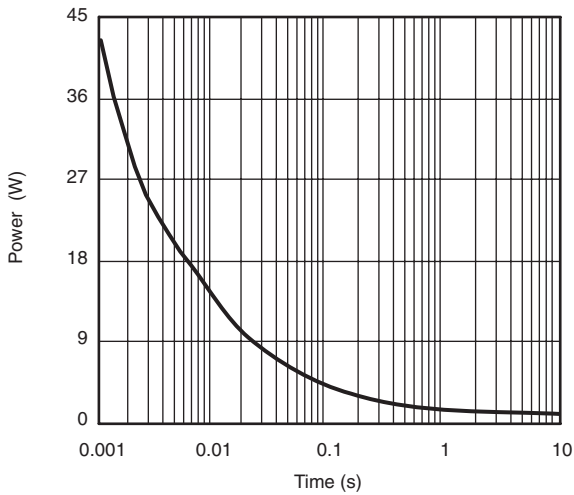
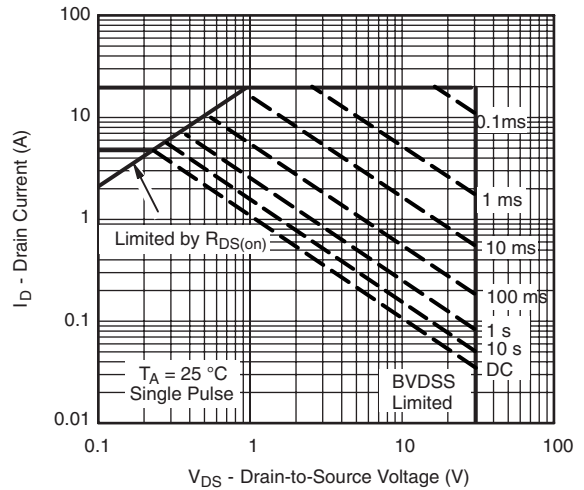
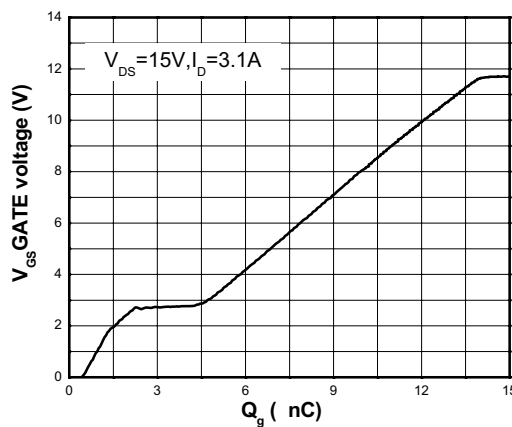
d Repetitive rating, pulse width limited by junction temperature $T_J=150^\circ\text{C}$.

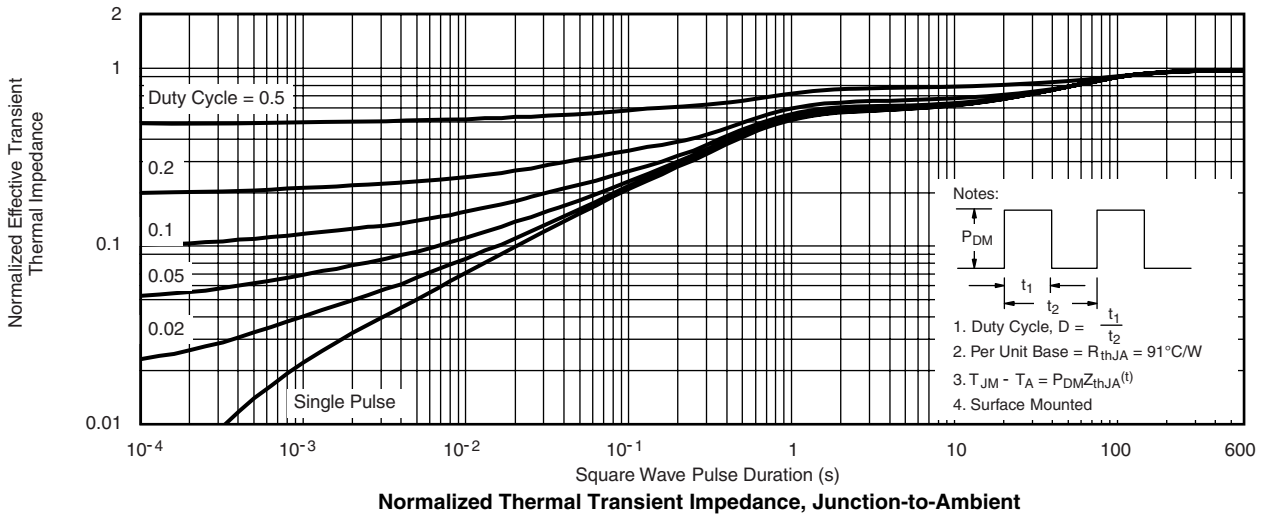
Electronics Characteristics

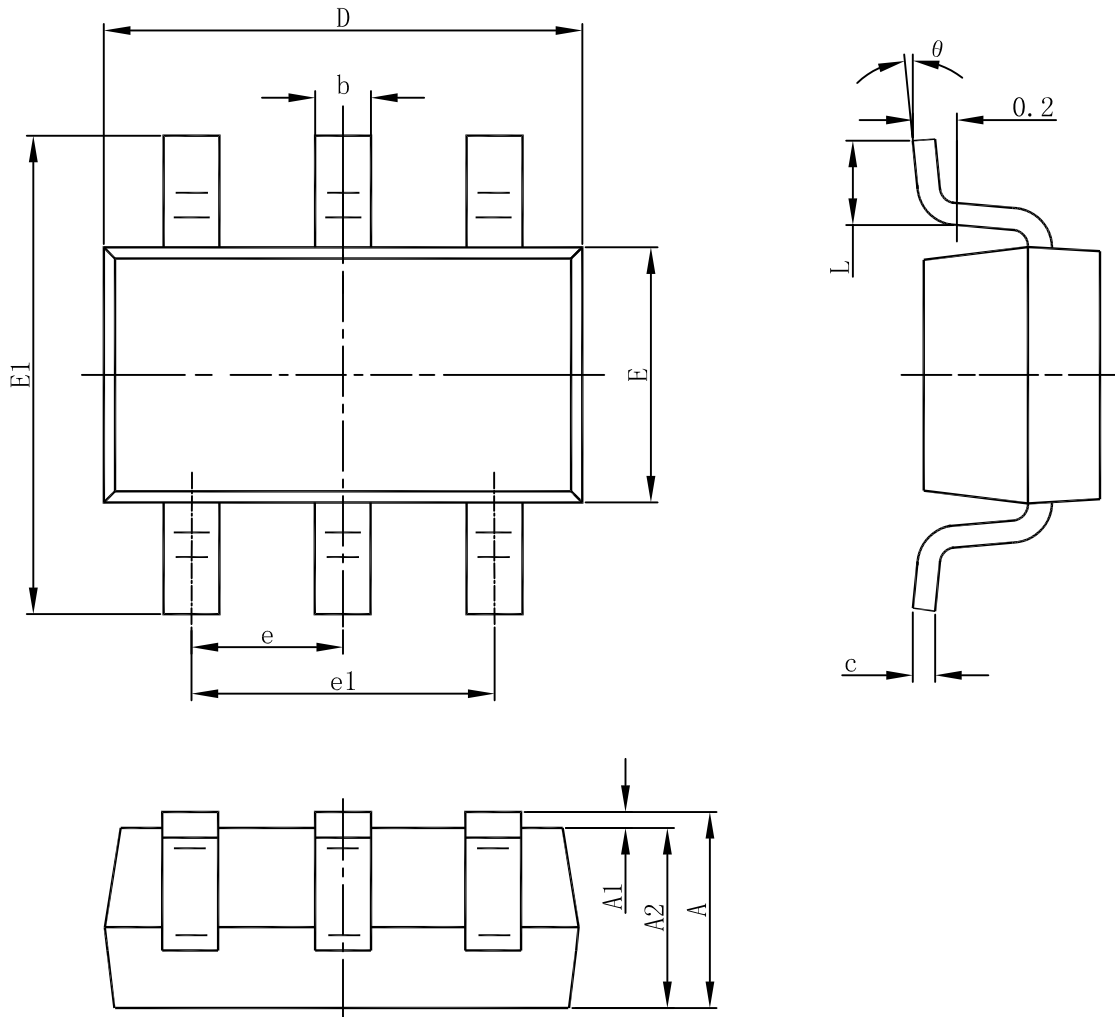
(Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250uA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	1.0	1.7	3.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 3.1A		28	47	mΩ
		V _{GS} = 4.5V, I _D = 2.0A		39	59	
Forward Transconductance	g _{FS}	V _{DS} = 4.5V, I _D = 2.8A		5.3		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 15 V		570		pF
Output Capacitance	C _{OSS}			72		
Reverse Transfer Capacitance	C _{RSS}			64		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 3.1A		11.6		nC
Threshold Gate Charge	Q _{G(TH)}			0.8		
Gate-to-Source Charge	Q _{GS}			1.25		
Gate-to-Drain Charge	Q _{GD}			3.0		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 1A, R _G = 6 Ω		5		ns
Rise Time	tr			3.3		
Turn-Off Delay Time	td(OFF)			39		
Fall Time	tf			4.4		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1.5A	0.50	0.84	1.50	V

Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature


Capacitance

Body diode forward voltage

Single pulse power

Safe operating power

Gate Charge Characteristics



Package Outline Dimension
SOT-23-6L


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	1.050	1.150	1.250
A1	0.000	0.050	0.100
A2	1.050	1.100	1.150
b	0.300	0.400	0.500
c	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
e	0.950(BSC)		
e1	1.800	1.900	2.000
L	0.300		0.600
theta	0°		8°